

RoHS

COMPLIANT

HALOGEN FREE Available

Vishay Siliconix

P-Channel 12-V (D-S) MOSFET

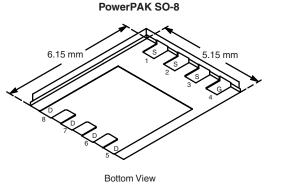
PRODUCT SUMMARY				
V _{DS} (V)	R _{DS(on)} (Ω)	I _D (A)		
	0.0065 at V _{GS} = - 4.5 V	- 21		
- 12	0.008 at V _{GS} = - 2.5 V	- 19		
	0.011 at V _{GS} = - 1.8V	- 16		

FEATURES

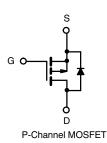
- Halogen-free According to IEC 61249-2-21
 Available
- TrenchFET[®] Power MOSFET
- New Low Thermal Resistance PowerPAK[®] Package with Low 1.07 mm Profile

APPLICATIONS

Load Switch



Ordering Information: Si7495DP-T1-E3 (Lead (Pb)-free) Si7495DP-T1-GE3 (Lead (Pb)-free and Halogen-free)



ABSOLUTE MAXIMUM RATINGS	T _A = 25 °C, unles	ss otherwise r	noted		
Parameter		Symbol	10 s	Steady State	Unit
Drain-Source Voltage		V _{DS}	- 12		V
Gate-Source Voltage		V _{GS}	± 8		
Continuous Drain Current (T 150 °C)	T _A = 25 °C	- I _D	- 21	- 13	٨
Continuous Drain Current (T _J = 150 °C) ^a	T _A = 70 °C		- 17	- 10	
Pulsed Drain Current		I _{DM}	- 50		A
Continuous Source Current (Diode Conduction) ^a		۱ _S	- 4.5	- 1.6	
Maximum Power Dissipation ^a	T _A = 25 °C	P _D	5	1.8	W
	T _A = 70 °C		3.2	1.1	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150		°C
Soldering Recommendations (Peak Temperature) ^{b, c}			260		C

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Maximum lumation to Ambianta	t ≤ 10 s	R _{thJA}	20	25	
Maximum Junction-to-Ambient ^a	Steady State		54	68	°C/W
Maximum Junction-to-Case (Drain)	Steady State	R _{thJC}	1.7	2.2	

Notes

a. Surface Mounted on 1" x 1" FR4 board.

b. See Solder Profile (<u>www.vishay.com/ppg?73257</u>). The PowerPAK SO-8 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.

c. Rework Conditions: manual soldering with a soldering iron is not recommended for leadless components.

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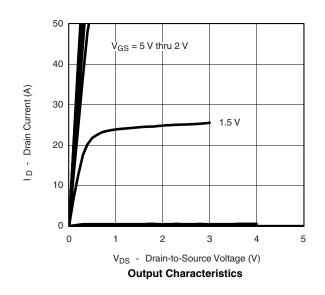
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Static				•			
Gate Threshold Voltage	V _{GS(th)}	$V_{GS(th)}$ $V_{DS} = V_{GS}$, $I_D = -1$ mA			- 0.9	V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 V, V_{GS} = \pm 8 V$			± 100	nA	
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = -12 V, V_{GS} = 0 V$			- 1	μA	
		V_{DS} = - 12 V, V_{GS} = 0 V, T_{J} = 70 °C			-10		
On-State Drain Current ^a	I _{D(on)}	$V_{DS}{\leq}$ - 5 V, V_{GS} = - 4.5 V	- 40			А	
Drain-Source On-State Resistance ^a		V _{GS} = - 4.5 V, I _D = - 21 A		0.0054	0.0065		
	R _{DS(on)}	V _{GS} = - 2.5 V, I _D = - 19 A		0.0065	0.008	Ω	
		V _{GS} = - 1.8 V, I _D = - 16 A		0.0088	0.011		
Forward Transconductance ^a	9 _{fs}	V _{DS} = - 15 V, I _D = - 21 A		80		S	
Diode Forward Voltage ^a	V _{SD}	$I_{\rm S}$ = - 4.5 A, $V_{\rm GS}$ = 0 V		- 0.65	- 1.1	V	
Dynamic ^b							
Total Gate Charge	Qg			93	140		
Gate-Source Charge	Q _{gs}	$V_{DS} = -6 V$, $V_{GS} = -5 V$, $I_{D} = -21 A$		10.5		nC	
Gate-Drain Charge	Q _{gd}			22			
Gate Resistance	Rg			2.7		Ω	
Turn-On Delay Time	t _{d(on)}			100	150		
Rise Time	tr	V_{DD} = - 6 V, R_L = 6 Ω		200	300	ns	
Turn-Off Delay Time	t _{d(off)}	$I_D \cong$ - 1 A, V_{GEN} = - 4.5 V, R_g = 6 Ω		350	530		
Fall Time	t _f			230	350		
Source-Drain Reverse Recovery Time	t _{rr}	I _F = - 2.9 A, dl/dt = 100 A/μs		110	165		

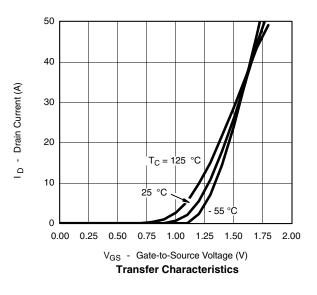
Notes:

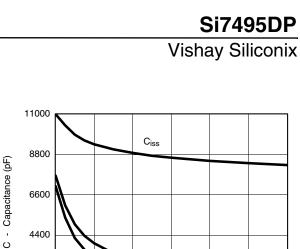
a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %. b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS 25 °C, unless noted







6600

4400

2200

0

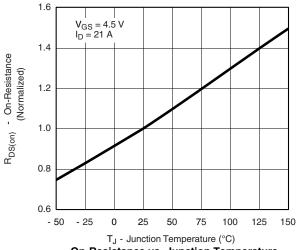
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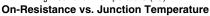
Crss

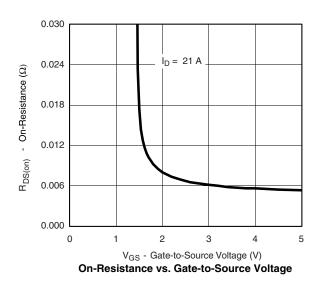


 C_{oss}

12

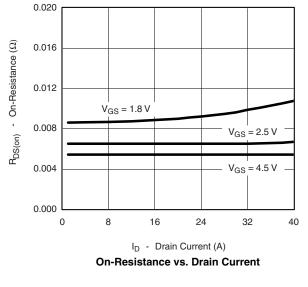


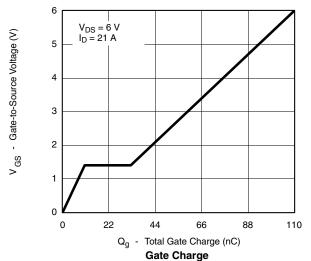


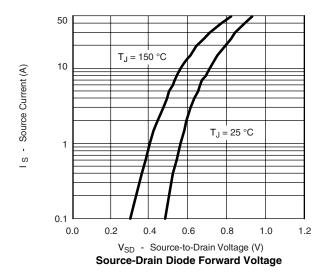




VISHAY



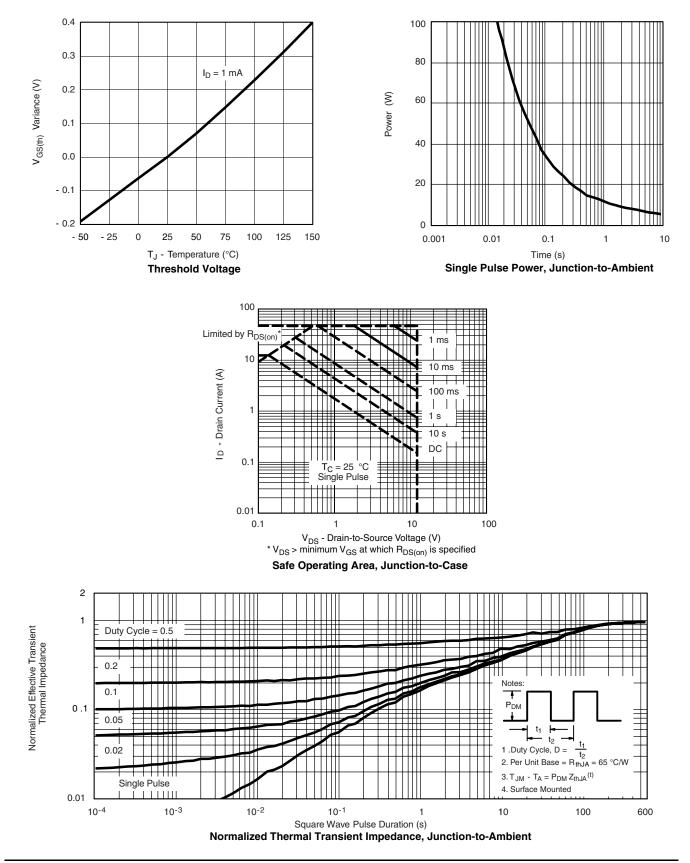




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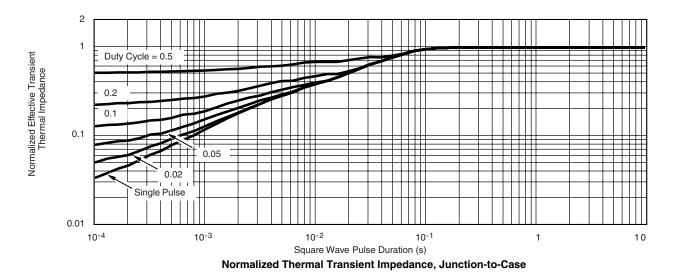






Si7495DP Vishay Siliconix

TYPICAL CHARACTERISTICS 25 °C, unless noted



Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see <u>www.vishay.com/ppg?72277</u>.



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